

JMSH04014G4L

Features

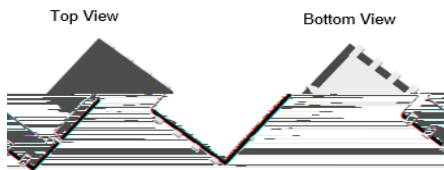
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS Tested
- 100% Vds Tested
- Halogen-free; RoHS-compliant

Applications

- Load Switch
- PWM Application
- Power Management

Product Summary

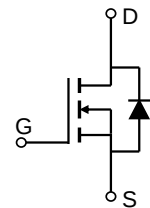
Parameters	Value	Unit
V_{DSS}	40	V
$V_{GS(th)}_{Typ}$	2.8	V
$I_D(@V_{GS}=10V)$	209	A
$R_{DS(ON)}_{Typ}(@V_{GS}=10V)$	1.2	m Ω



PDFN5X6-8L



Pin Assignment



Schematic Diagram

Ordering Information

Device	Marking	MSL	Form	Package	Reel(pcs)	Per Carton (pcs)
JMSH04014G4L-13	SH040144L	1	Tape&Reel	PDFN5x6-8L	5000	50000

Absolute Maximum Ratings (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter		Value	Unit
V _{DS}	Drain-to-Source Voltage		40	V
V _{GS}	Gate-to-Source Voltage		±20	V
I _D	Continuous Drain Current	T _C = 25°C	209	A
		T _C = 100°C	148	
I _{DM}	Pulsed Drain Current ⁽¹⁾		Refer to Fig.4	A
E _{AS}	Single Pulsed Avalanche Energy ⁽²⁾		389	mJ
P _D	Power Dissipation	T _C = 25°C	107	W
		T _C = 100°C	54	
T _J , T _{STG}	Junction & Storage Temperature Range		-55 to 175	°C

Thermal Characteristics

Symbol	Parameter	Max	Unit
R	Thermal Resistance, Junction to Ambient ⁽³⁾	46	$^\circ\text{C/W}$
R	Thermal Resistance, Junction to Case	1.4	$^\circ\text{C/W}$

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	I _D = 250μA, V _{GS} = 0V	40	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 32V, V _{GS} = 0V	-	-	1.0	μA
I _{GSS}	Gate-Body Leakage Current	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	2.0	2.8	4.0	V
R _{DS(ON)}	Static Drain-Source ON-Resistance ⁽⁴⁾	V _{GS} = 10V, I _D = 20A	-	1.2	1.4	mΩ
Dynamic Characteristics						
R _g	Gate Resistance	f = 1MHz	-	1.9	-	Ω
C _{iss}	Input Capacitance	V _{GS} = 0V, V _{DS} = 20V, f = 1MHz	-	3859	5250	pF
C _{oss}	Output Capacitance		-	1129	1550	pF
C _{rss}	Reverse Transfer Capacitance		-	70	150	pF
Q _g	Total Gate Charge	V _{GS} = 0 to 10V V _{DS} = 20V, I _D = 20A	-	59	-	nC
Q _{gs}	Gate Source Charge		-	16	-	nC
Q _{gd}	Gate Drain("Miller") Charge		-	12	-	nC
Switching Characteristics						
t _{d(on)}	Turn-On DelayTime	V _{GS} = 10V, V _{DD} = 20V I _D = 20A, R _{GEN} = 3Ω	-	25	-	ns
t _r	Turn-On Rise Time		-	26	-	ns
t _{d(off)}	Turn-Off DelayTime		-	38	-	ns
t _f	Turn-Off Fall Time		-	12	-	ns
Body Diode Characteristics						
I _S	Maximum Continuous Body Diode Forward Current		-	-	209	A
I _{SM}	Maximum Pulsed Body Diode Forward Current		-	-	836	A
V _{SD}	Body Diode Forward Voltage	V _{GS} = 0V, I _S = 20A	-		1.2	V
trr	Body Diode Reverse Recovery Time	I _F = 20A, di/dt = 100A/us	21	41	62	ns
Qrr	Body Diode Reverse Recovery Charge		-	41	-	nC

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
 2. E_{AS} condition: Starting $T_J = 25^\circ\text{C}$, $V_{DD} = 20\text{V}$, $V_{GS} = 10\text{V}$, $R_G = 25\text{ohm}$, $L = 3\text{mH}$, $I_{AS} = 16.1\text{A}$, $V_{DD} = 0\text{V}$ during time in avalanche.
 3. R is measured with the device mounted on a 1inch^2 pad of 2oz copper FR4 PCB.
 4. Pulse Test: Pulse Width $\leq$ $\leq 0.5\%$.

Typical Performance Characteristics

Figure 1: Power De-rating

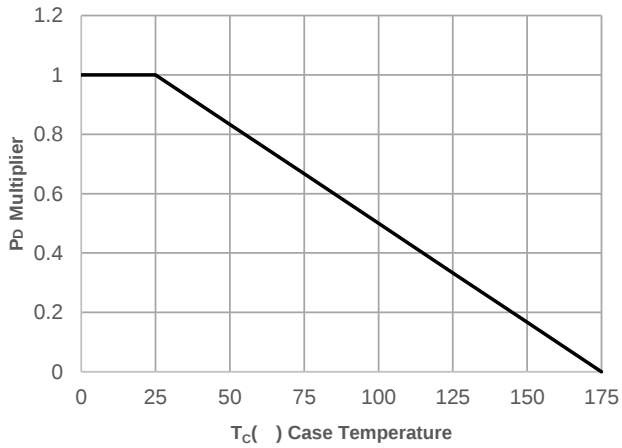


Figure 2: Current De-rating

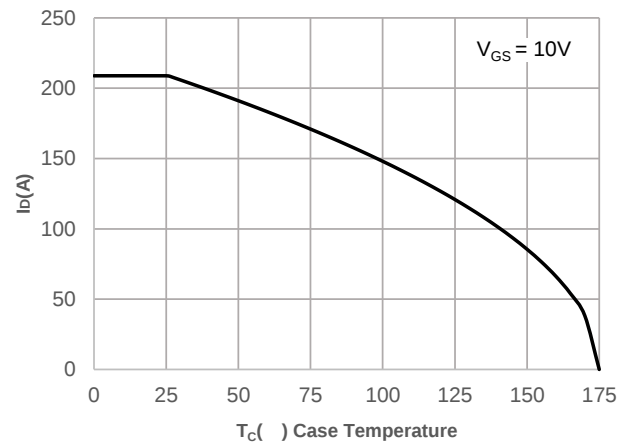


Figure 3: Normalized Maximum Transient Thermal Impedance

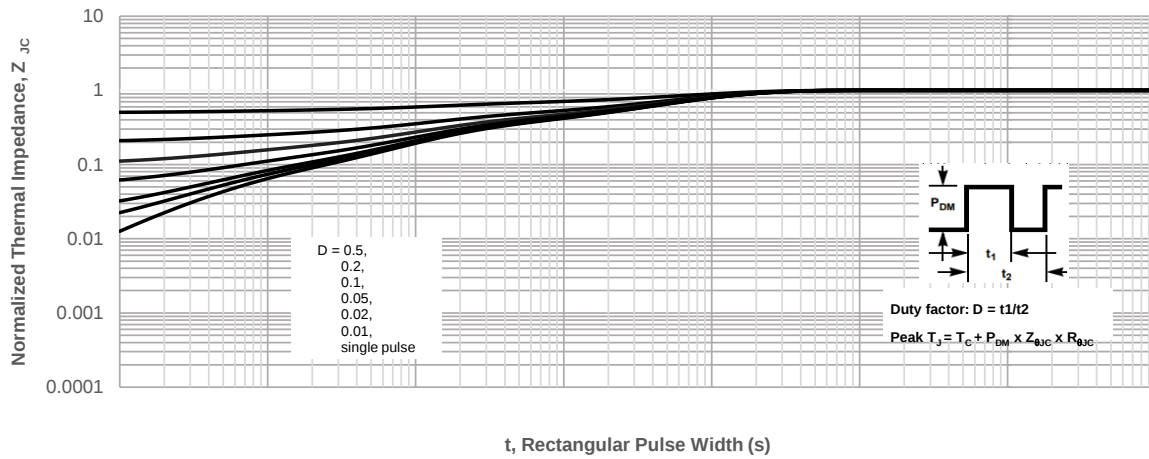
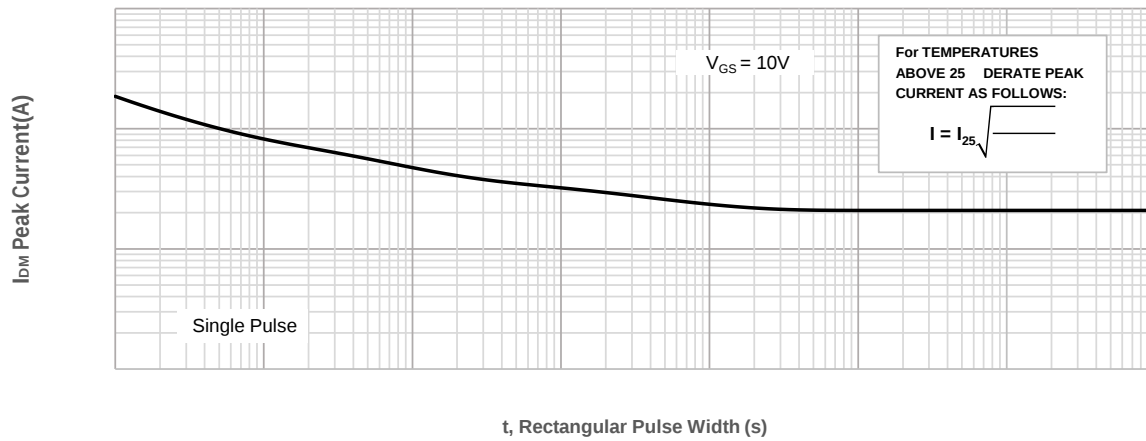


Figure 4: Peak Current Capacity



Typical Performance Characteristics

Figure 11: Normalized Breakdown Voltage vs. Junction Temperature

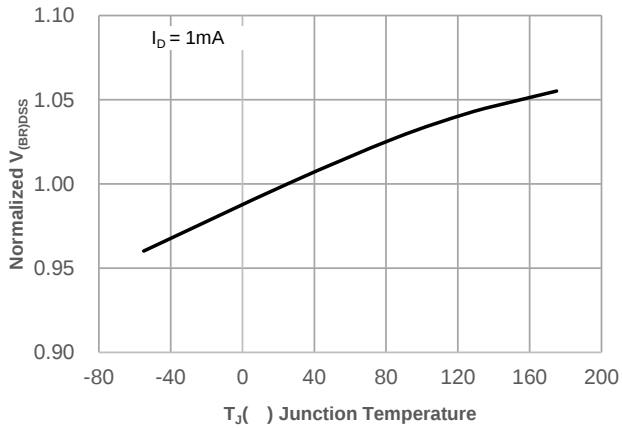


Figure 12: Normalized on Resistance vs. Junction Temperature

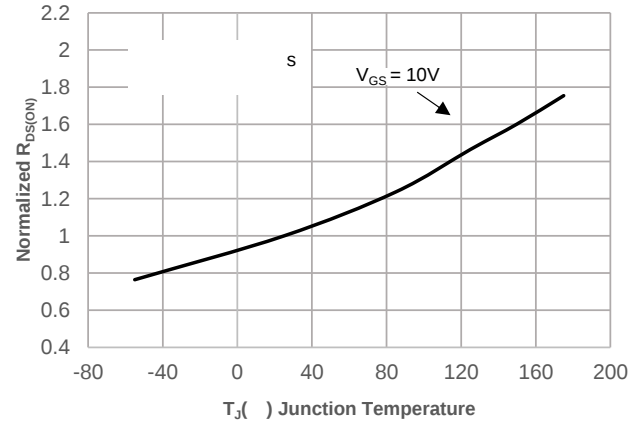


Figure 13: Normalized Threshold Voltage vs. Junction Temperature

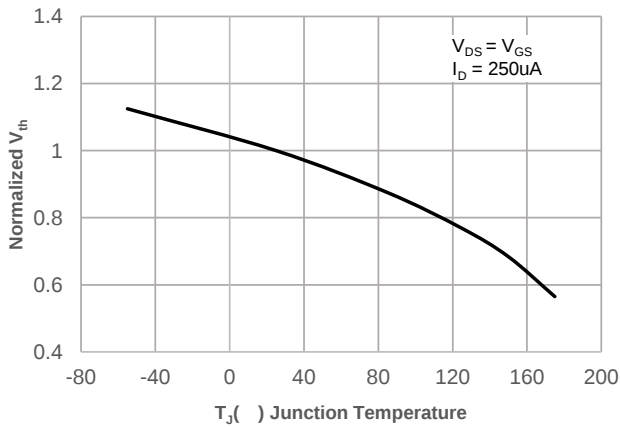


Figure 14: $R_{DS(ON)}$ vs. V_{GS}

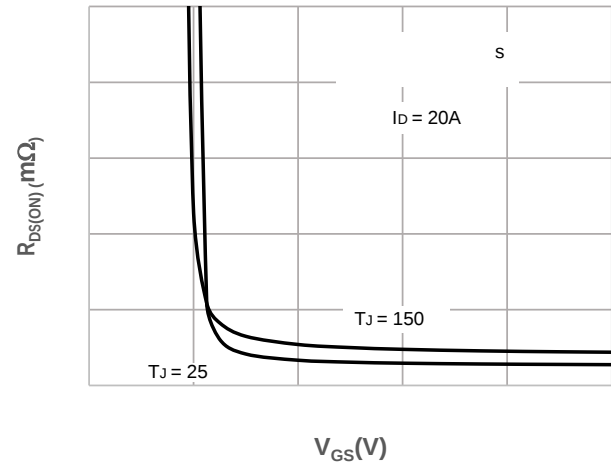
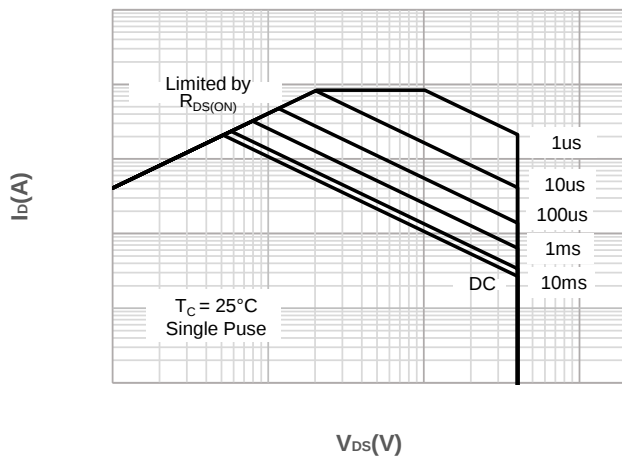


Figure 15: Maximum Safe Operating Area



Test Circuit



Figure 1: Gate Charge Test Circuit & Waveform

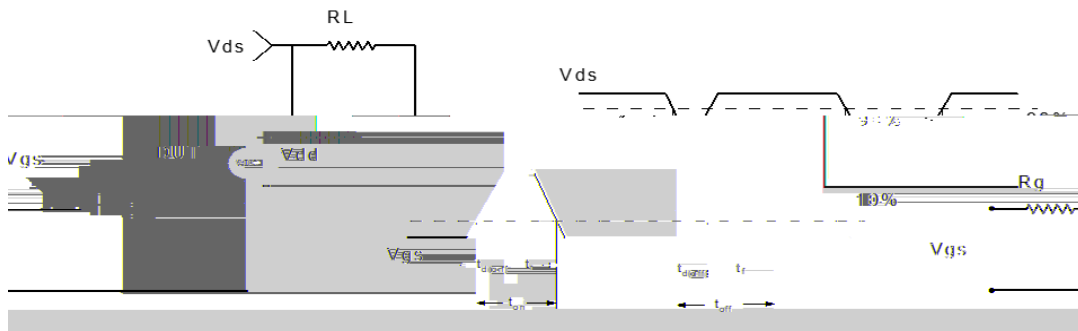


Figure 2: Resistive Switching Test Circuit & Waveform

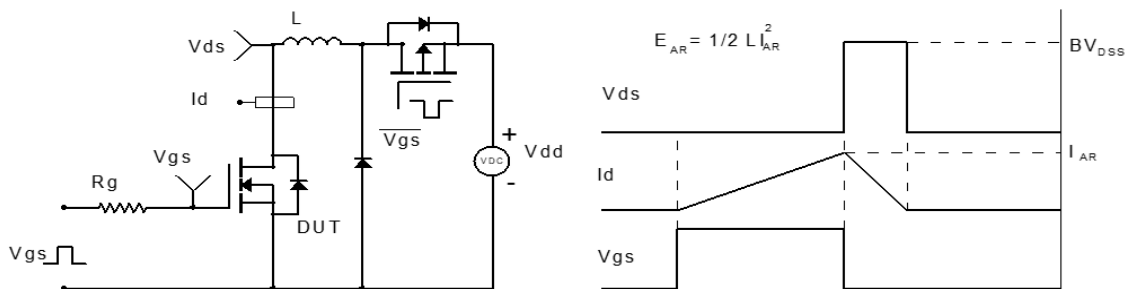


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

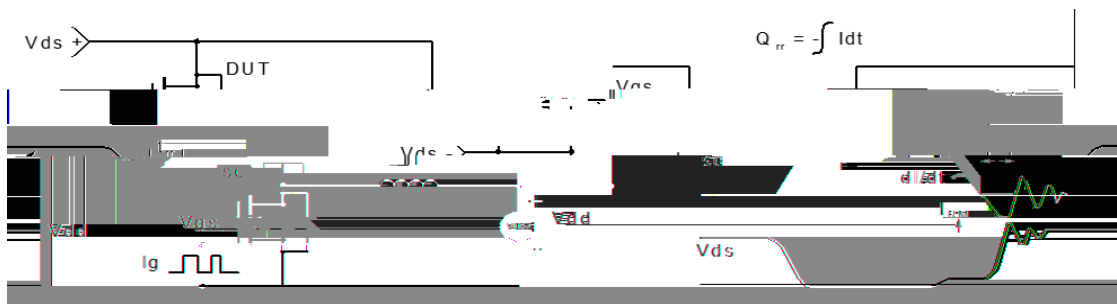
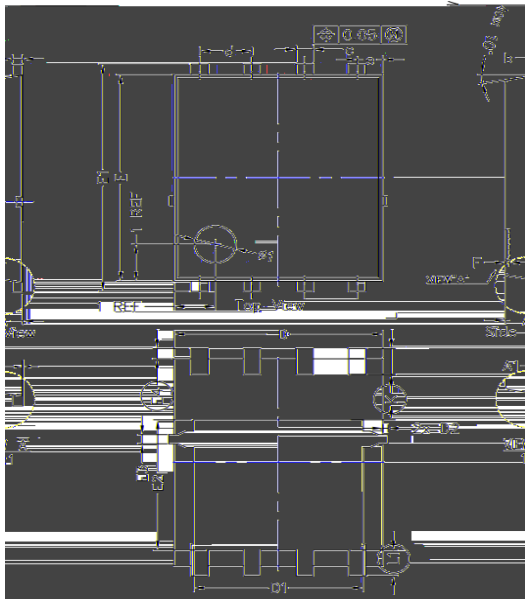


Figure 4: Diode Recovery Test Circuit & Waveform



Package Mechanical Data(PDFN5X6-8L)



SYMBOLS	DIMENSIONS (mm)			DIMENSIONS (inches)		
	MIN	NOM	MAX	MIN	NOM	MAX
*A	0.900	1.000	1.150	0.035	0.039	0.045
A1	0.000		0.050	0.000		0.002
b	0.246	0.254	0.350	0.010	0.010	0.014
c	0.640	0.630	0.640	0.025	0.025	0.025
d		1.270SC			0.050SC	
*D	3.950	5.050	5.150	0.155	0.199	0.203
D1	4.000	4.100	4.200	0.157	0.161	0.165
D2		0.125REF			0.005REF	
e		0.628SC			0.0249SC	
*E	5.500	5.600	5.700	0.217	0.220	0.224
F	0.524	0.524	0.524	0.021	0.021	0.021
G	0.130	0.130	0.130	0.005	0.005	0.005
H	0.000	0.000	0.000	0.000	0.000	0.000
I	0.000	0.000	0.000	0.000	0.000	0.000
J	0.000	0.000	0.000	0.000	0.000	0.000



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